

L Number	Hits	Search Text	DB	Time stamp
1	2	VCO and diffusion and "p material"	USPAT	2004/02/13 12:07
2	212	438/200.ccls.	USPAT	2004/02/13 12:08
3	117	438/200.ccls. and diffusion	USPAT	2004/02/13 12:09
4	109	438/200.ccls. and diffusion and gate	USPAT	2004/02/13 12:09
5	84	438/200.ccls. and diffusion and gate and CMOS	USPAT	2004/02/13 12:09
6	0	438/200.ccls. and diffusion and gate and CMOS and inductors	USPAT	2004/02/13 12:09
7	0	438/200.ccls. and diffusion and gate and CMOS and VCO	USPAT	2004/02/13 12:09
8	0	438/200.ccls. and VCO	USPAT	2004/02/13 12:10
9	1	438/200.ccls. and inductors	USPAT	2004/02/13 12:10
-	14147	VCO	USPAT	2003/12/22 10:09
-	310	VCO and diffusion	USPAT	2003/12/22 10:09
-	1	VCO and diffusion and "p material" and CMOS	USPAT	2003/12/22 10:33
-	55381	CMOS	USPAT	2003/12/22 10:34
-	8	CMOS and "rectangular diffusion"	USPAT	2003/12/22 10:34
-	2	CMOS and "rectangular diffusion" and material and well	USPAT	2003/12/22 10:34
-	2	CMOS and "rectangular diffusion" and material and well and gate	USPAT	2003/12/22 10:34
-	2	CMOS and "rectangular diffusion" and material and well and gate and substrate	USPAT	2003/12/22 10:38
-	12246	CMOS and diffusion	USPAT	2003/12/22 10:38
-	8246	CMOS and diffusion and material	USPAT	2003/12/22 10:38
-	7279	CMOS and diffusion and material and well	USPAT	2003/12/22 10:38
-	6958	CMOS and diffusion and material and well and substrate	USPAT	2003/12/22 10:38
-	5987	CMOS and diffusion and material and well and substrate and gate	USPAT	2003/12/22 10:39
-	555	CMOS and diffusion and material and well and substrate and gate and polycide	USPAT	2003/12/22 10:43
-	0	CMOS and diffusion and material and well and substrate and gate and polycide and vco	USPAT	2003/12/22 10:39
-	0	CMOS and diffusion and material and well and substrate and gate and polycide and VCO	USPAT	2003/12/22 10:39
-	2	CMOS and diffusion and "p material" and well and substrate and gate and polycide	USPAT	2003/12/22 10:44